

COMPLIANT

Phase Control Thyristors (Hockey PUK Version), 1745 A



K-PUK (A-24)

PRIMARY CHARACTERISTICS					
I _{T(AV)}	1745 A				
V_{DRM}/V_{RRM}	800 V, 1200 V, 1400 V, 1600 V				
V_{TM}	1.62 V				
I _{GT}	100 mA				
T _J	-40 °C to +125 °C				
Package	K-PUK (A-24)				
Circuit configuration	Single SCR				

FEATURES

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case K-PUK (A-24)
- High profile hockey PUK
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		1745	А		
$I_{T(AV)}$	T _{hs}	55	°C		
1		3200	A		
IT(RMS)	T _{hs}	25	°C		
I _{TSM}	50 Hz	33 500	^		
	60 Hz	35 100	A		
124	50 Hz	5615	kA ² s		
l ² t	60 Hz	5126			
V _{DRM} /V _{RRM}		800 to 1600	V		
tq	Typical	200	μs		
T _J		-40 to +125	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA				
	08	800	900					
VS-ST1230CK	12	1200	1300	100				
V3-3112300K	14	1400	1500	100				
	16	1600	1700					



PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS		
Maximum average on-state current		180° condu	180° conduction, half sine wave		180° conduction, half sine wave			Α
at heatsink temperature	I _{T(AV)}	double side	(single side) co	oled	55 (85)	°C		
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink tempe	erature double side cooled	3200			
		t = 10 ms	No voltage		33 500			
Maximum peak, one-cycle		t = 8.3 ms	reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	35 100	A		
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		28 200			
		t = 8.3 ms	reapplied		29 500			
Maximum I ² t for fusing		t = 10 ms	No voltage reapplied		5615	- kA ² s		
	l ² t	t = 8.3 ms			5126			
		t = 10 ms			3971			
		t = 8.3 ms	reapplied		3625			
Maximum I ² √t for fusing	I²√t	t = 0.1 to 10) ms, no voltage	reapplied	56 150	kA²√s		
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.93	V		
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$), $T_J = T_J$ maxin	num	1.02] v		
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.17	mΩ		
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.16	11122		
Maximum on-state voltage	V_{TM}	$I_{pk} = 4000 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$			1.62	V		
Maximum holding current	I _H	T. = 25 °C	T 05.00 and a 14.00 and the land			mA		
Typical latching current	ΙL	T _J = 25 °C, anode supply 12 V resistive load			1000	IIIA		

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/μs			
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1$ A/ μ s $V_d = 0.67$ % V_{DRM} , $T_J = 25$ °C	1.9				
Typical turn-off time	t _q	I_{TM} = 550 A, T_J = T_J maximum, dI/dt = 40 A/ μ s, V_R = 50 V, dV/dt = 20 V/ μ s, gate 0 V 100 Ω , t_p = 500 μ s	200	μs			

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	100	mA



TRIGGERING						
DADAMETED	SYMBOL	TECT COMPITIONS		VALUES		LINUTO
PARAMETER	STMBOL	15	ST CONDITIONS	typ.	Max.	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum,	$t_p \leq 5 \; ms$	1	6	w
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	(3] vv
Maximum peak positive gate current	I _{GM}			3	.0	Α
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms		0	V	
Maximum peak negative gate voltage	- V _{GM}			5	.0	ľ
		T _J = -40 °C	Maximum required gate trigger/ current/voltage are the lowest	200	-	mA
DC gate current required to trigger	I _{GT}	T _J = 25 °C		100	200	
		T _J = 125 °C		50	-	
		T _J = -40 °C	value which will trigger all units	1.4	-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	12 V anode to cathode applied	1.1	3.0	V
		T _J = 125 °C		0.9	-	
DC gate current not to trigger	I _{GD}		Maximum gate current/	10		mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J \text{ maximum}$	voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to 125	°C		
Maximum storage temperature range	T _{Stg}		-40 to 150			
Maximum thermal resistance, junction to heatsink	R _{thJ-hs}	DC operation single side cooled	0.042			
		DC operation double side cooled	0.021	K/W		
Maximum thermal resistance.	R _{thC-hs}	DC operation single side cooled	0.006			
case to heatsink		DC operation double side cooled	0.003			
Mounting force, ± 10 %			24 500 (2500)	N (kg)		
Approximate weight			425	g		
Case style		See dimensions - link at the end of datasheet K-PU		-24)		

△R _{thJC} CONDUCTION								
CONDUCTION ANGLE	CONDUCTION ANGLE SINUSO CONDUCTION ANGLE				TEST CONDITIONS	UNITS		
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE				
180°	0.003	0.003	0.002	0.002				
120°	0.004	0.004	0.004	0.004				
90°	0.005	0.005	0.005	0.005	$T_J = T_J$ maximum	K/W		
60°	0.007	0.007	0.007	0.007				
30°	0.012	0.012	0.012	0.012				

Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

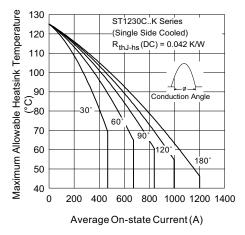


Fig. 1 - Current Ratings Characteristics

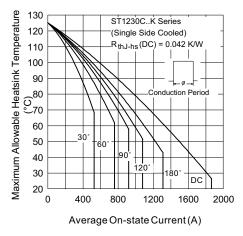


Fig. 2 - Current Ratings Characteristics

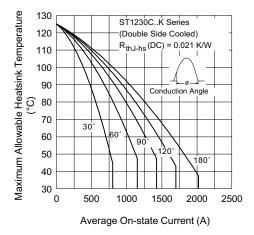


Fig. 3 - Current Ratings Characteristics

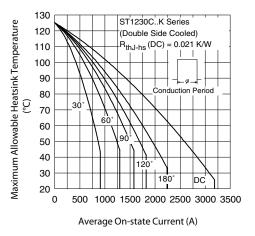


Fig. 4 - Current Ratings Characteristics

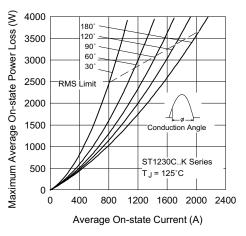


Fig. 5 - On-State Power Loss Characteristics

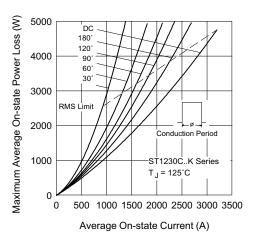
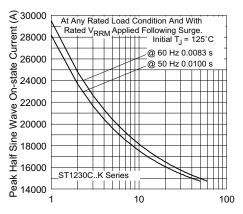


Fig. 6 - On-State Power Loss Characteristics



Number Of Equal Amplitude Half Cycle Current Pulses (N)

Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

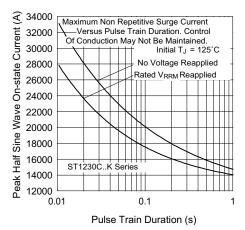


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

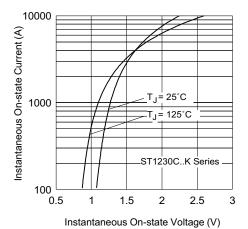


Fig. 9 - On-State Voltage Drop Characteristics

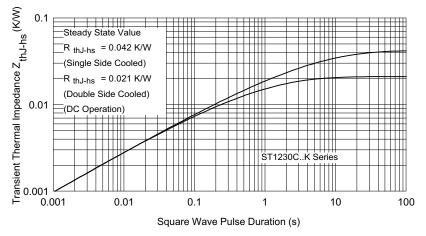


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

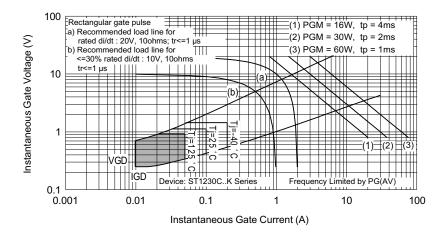
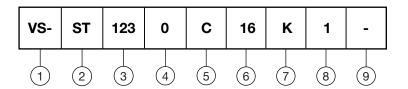


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

4 - 0 = converter grade

5 - C = ceramic PUK

6 - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)

7 - K = PUK case K-PUK (A-24)

8 - 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

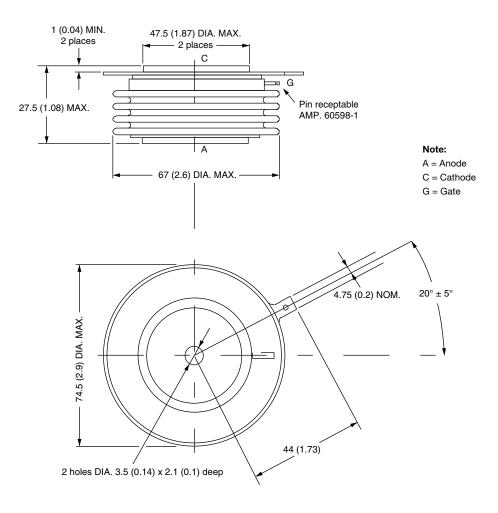
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95081			



K-PUK (A-24)

DIMENSIONS in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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